YJ Planar Fast Recovery Diode Die Specification

400V 75A, Fast recovery diode die based on silicon planar process

Part No.: FRD75A400AS-290A

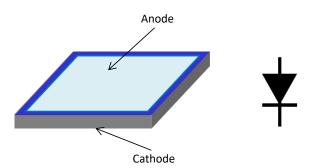
Main Products Characterstics

• Average forward current: IF(AV) = 75A

• Maximum operating junction temperature: Tj = 150 °C

Planar Construction

• Top metal: Al



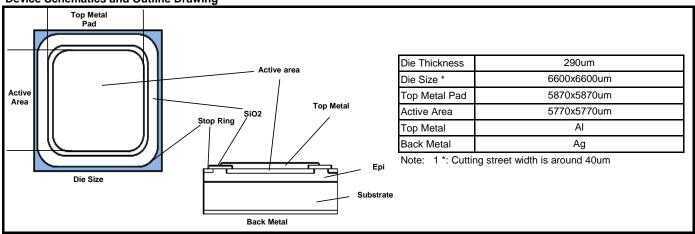
Maximum Ratings

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Parameter	Symbol	Rating		
Repetitive peak reverse voltage	V_{RRM}	400V		
Average forward current	$I_{F(AV)}$	75A		
Non-repetitive peak surge current (tp = 8.3 ms, halfwave, 1 cycle)	I _{FSM}	700A		
Storage temperature range	T_{stg}	-40 to +150 °C		
Maximum operating junction temperature	T _j	150 °C		

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value	
Faranietei	Symbol	Spec	Typical
Reverse breakdown voltage $I_R = 50$ uA	V_{BR}	420V	440V
Maximum forward voltage drop I_F = 20A, Pulse Test: tp = 380 $\mu s, \ \delta \leqslant 2\%$	V _F	1.0V	0.95V
Reverse Recovery Time $I_F=0.5A$, $I_R=1A$, $I_{rr}=0.25A$	Trr	75ns	58ns
Maximum reverse current $V_R = V_{RRM}$ Pulse Test: tp = 10 ms, $\delta \leqslant 2\%$	I _R	2uA	0.05uA

Device Schematics and Outline Drawing



Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangjie Electronics does not guarantee device performance after assembly.

All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.